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Texas Instruments CSD16323Q3

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N-Channel NexFET[™] Power MOSFETs

Check for Samples: CSD16323Q3

FEATURES

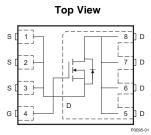
- **Optimized for 5V Gate Drive**
- Ultra Low Qg and Qgd
- Low Thermal Resistance
- **Avalanche Rated**
- **Pb Free Terminal Plating**
- **RoHS Compliant**
- **Halogen Free**
- SON 3.3mm x 3.3mm Plastic Package

APPLICATIONS

- Point-of-Load Synchronous Buck Converter for Applications in Networking, Telecom and **Computing Systems**
- **Optimized for Control or Synchronous FET** Applications

DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion and optimized for 5V gate drive applications.



PRODUCT SUMMARY

V _{DS}	Drain to Source Voltage 25					
Qg	Gate Charge Total (4.5V) 6.2					
Q_{gd}	Gate Charge Gate to Drain	1.1		nC		
		$V_{GS} = 3V$	5.4	mΩ		
R _{DS(on)}	Drain to Source On Resistance	$V_{GS} = 4.5V$	4.4	mΩ		
		$V_{GS} = 8V$	3.8	mΩ		
V _{th}	Threshold Voltage	1.1		V		

ORDERING INFORMATION

Device	Package	Media	Qty	Ship
CSD16323Q3	SON 3.3 × 3.3 Plastic Package	13-inch reel	2500	Tape and Reel

ABSOLUTE MAXIMUM RATINGS

$T_A = 2$	5°C unless otherwise stated	VALUE	UNIT
V_{DS}	Drain to Source Voltage	25	V
V_{GS}	Gate to Source Voltage	+10 /8	V
	Continuous Drain Current, T _C = 25°C	60	А
ID	Continuous Drain Current ⁽¹⁾	21	А
I _{DM}	Pulsed Drain Current, $T_A = 25^{\circ}C^{(2)}$	112	А
PD	Power Dissipation ⁽¹⁾	3	W
T _J , T _{STG}	Operating Junction and Storage Temperature Range	–55 to 150	°C
E _{AS}	Avalanche Energy, single pulse $I_D = 50A$, L = 0.1mH, R _G = 25 Ω	125	mJ

(1) $R_{\theta JA} = 43^{\circ}C/W$ on $1in^2$ Cu (2 oz.) on 0.060" thick FR4 PCB.

(2) Pulse width ≤300µs, duty cycle ≤2%



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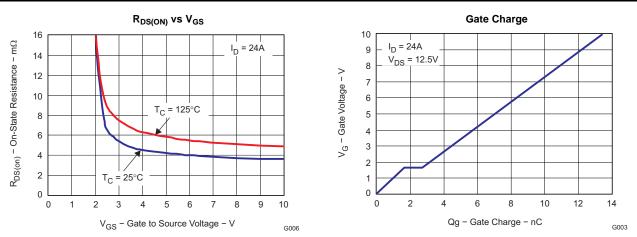


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TEXAS INSTRUMENTS

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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

	°C unless otherwise stated) PARAMETER	TEST CONDITIONS	MIN	TYP	МАХ	UNIT
Static C	haracteristics	TEST CONDITIONS		IIF		
BV _{DSS}	Drain to Source Voltage	$V_{GS} = 0V, I_{D} = 250\mu A$	25			V
	Ŭ		20		1	
IDSS	Drain to Source Leakage Current	$V_{GS} = 0V, V_{DS} = 20V$				μA
I _{GSS}	Gate to Source Leakage Current	$V_{DS} = 0V, V_{GS} = +10/-8V$			100	nA
V _{GS(th)}	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	0.9	1.1	1.4	V
		$V_{GS} = 3V, I_D = 24A$		5.4	7.2	mΩ
R _{DS(on)}	Drain to Source On Resistance	$V_{GS} = 4.5V, I_{D} = 24A$		4.4	5.5	mΩ
		$V_{GS} = 8V, I_D = 24A$		3.8	4.5	mΩ
9 _{fs}	Transconductance	$V_{DS} = 12.5V, I_D = 24A$		108		S
Dynamic	c Characteristics					
C _{ISS}	Input Capacitance			1020	1300	pF
C _{OSS}	Output Capacitance	V _{GS} = 0V, V _{DS} = 12.5V, f = 1MHz		740	960	pF
C _{RSS}	Reverse Transfer Capacitance			50	65	pF
R _g	Series Gate Resistance			1.4	2.8	Ω
Qg	Gate Charge Total (4.5V)			6.2	8.4	nC
Q _{gd}	Gate Charge Gate to Drain			1.1		nC
Q _{gs}	Gate Charge Gate to Source	$V_{\rm DS} = 12.5 \text{V}, \text{ I}_{\rm D} = 24 \text{A}$		1.8		nC
Qg(th)	Gate Charge at Vth			1		nC
Q _{OSS}	Output Charge	V _{DS} = 12.5V, V _{GS} = 0V		14		nC
t _{d(on)}	Turn On Delay Time			5.3		ns
t _r	Rise Time	V _{DS} = 12.5V, V _{GS} = 4.5V I _D = 24A		15		ns
t _{d(off)}	Turn Off Delay Time	$R_{G} = 2\Omega$		13		ns
t _f	Fall Time			6.3		ns
	haracteristics					
V _{SD}	Diode Forward Voltage	I _S = 24A, V _{GS} = 0V		0.85	1	V
Q _{rr}	Reverse Recovery Charge	V _{DD} = 12.5V, I _F = 24A, di/dt = 300A/µs		21		nC
t _{rr}	Reverse Recovery Time	V _{DD} = 12.5V, I _F = 24A, di/dt = 300A/µs		16		ns



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THERMAL INFORMATION

	THERMAL METRIC ⁽¹⁾⁽²⁾	CSD16323Q3	
		8 PINS	UNITS
θ_{JA}	Junction-to-ambient thermal resistance	42.0	
θ_{JCtop}	Junction-to-case (top) thermal resistance	20.6	
θ_{JB}	Junction-to-board thermal resistance	8.8	°C/W
ΨJT	Junction-to-top characterization parameter	0.3	C/VV
Ψ _{JB}	Junction-to-board characterization parameter	8.7	
θ_{JCbot}	Junction-to-case (bottom) thermal resistance	0.1	

For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, SPRA953.
 For thermal estimates of this device based on PCB copper area, see the TI PCB Thermal Calculator.



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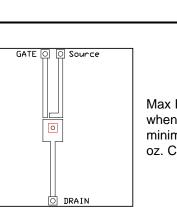
GATE Օ

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🖸 Source

DRAIN

M0161-0



Max $R_{\theta JA} = 162^{\circ}C/W$ when mounted on minimum pad area of 2 oz. Cu.

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G012

TYPICAL MOSFET CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

Max $R_{\theta JA} = 58^{\circ}C/W$ when mounted on 1

inch² of 2 oz. Cu.

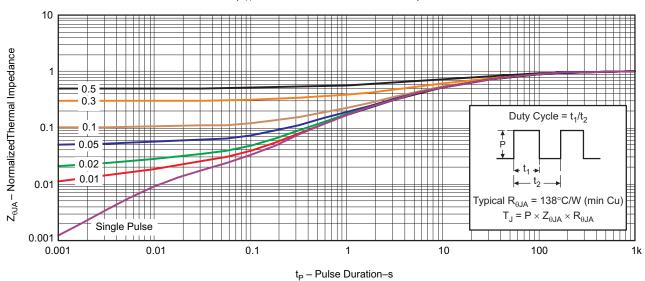


Figure 1. Transient Thermal Impedance



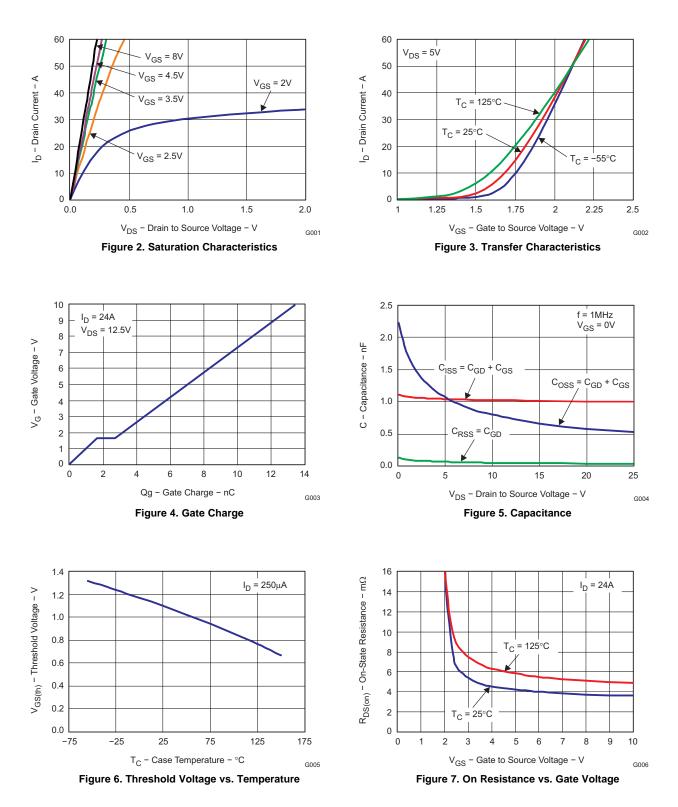
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TYPICAL MOSFET CHARACTERISTICS (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$



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TYPICAL MOSFET CHARACTERISTICS (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

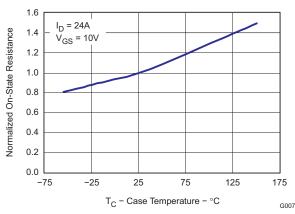


Figure 8. Normalized On Resistance vs. Temperature

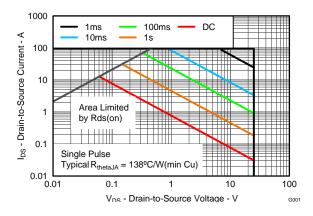


Figure 10. Maximum Safe Operating Area

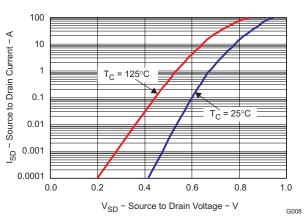


Figure 9. Typical Diode Forward Voltage

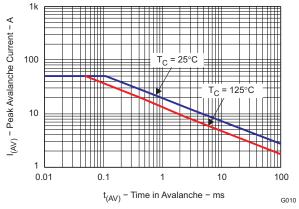
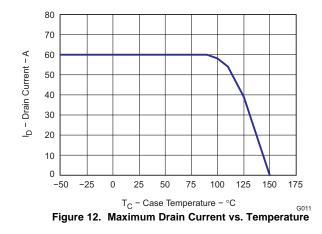


Figure 11. Single Pulse Unclamped Inductive Switching





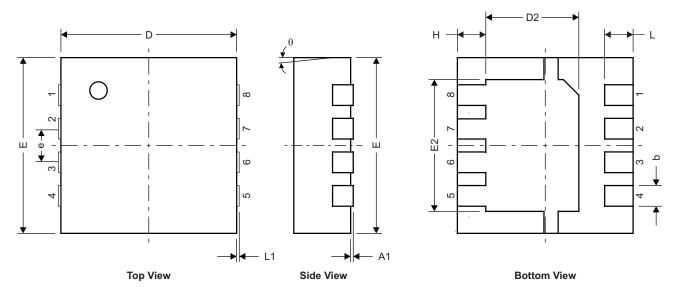
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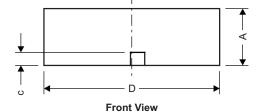
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MECHANICAL DATA

Q3 Package Dimensions





M0142-01

7

DIM		MILLIMETERS	6	INCHES			
	MIN	NOM	MAX	MIN	NOM	MAX	
А	0.950	1.000	1.100	0.037	0.039	0.043	
A1	0.000	0.000	0.050	0.000	0.000	0.002	
b	0.280	0.340	0.400	0.011	0.013	0.016	
С	0.150	0.200	0.250	0.006	0.008	0.010	
D	3.200	3.300	3.400	0.126	0.130	0.134	
D1	-	-	-	_	_	_	
D2	1.650	1.750	1.800	0.065	0.069	0.071	
Е	3.200	3.300	3.400	0.126	0.130	0.134	
E1	-	-	-	_	-	_	
E2	2.350	2.450	2.550	0.093	0.096	0.100	
е		0.650 TYP			0.026		
Н	0.35	0.450	0.550	0.014	0.018	0.022	
L	0.35	0.450	0.550	0.014	0.018	0.022	
L1	-	-	_	-	_	_	
θ	-	-	-	-	_	-	

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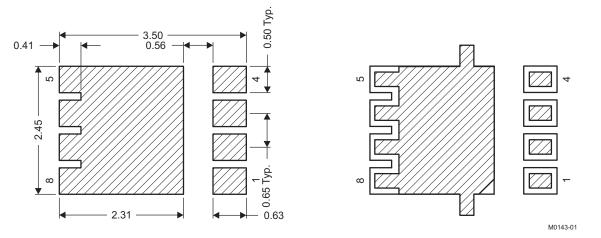
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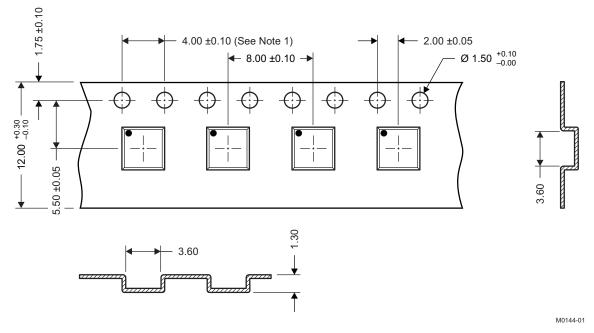
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Recommended PCB Pattern



For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.

Q3 Tape and Reel Information



Notes:

- 1. 10 sprocket hole pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1mm IN 100mm, noncumulative over 250mm
- 3. Material:black static dissipative polystyrene
- 4. All dimensions are in mm (unless otherwise specified)
- 5. Thickness: 0.30 ±0.05mm
- 6. MSL1 260°C (IR and Convection) PbF Reflow Compatible



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REVISION HISTORY

Changes from Original (August 2009) to Revision A	Page
 Changed R_{DS(on)} - V_{GS} = 3V, I_D = 24A MAX value From: 6.5 To: 7.2 Deleted the Package Marking Information section 	
Changes from Revision A (April 2010) to Revision B	
Replaced the THERMAL CHARACTERISTICS table with the new Thermal Information Table	Page



7-Jan-2016

PACKAGING INFORMATION

Orderable Device	Status	Package Type	•	Pins	•	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
CSD16323Q3	ACTIVE	VSON-CLIP	DQG	8	2500	Pb-Free (RoHS Exempt)	CU SN	Level-1-260C-UNLIM	-55 to 150	CSD16323	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs. LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design. PREVIEW: Device has been announced but is not in production. Samples may or may not be available. OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details. **TBD:** The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above. Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight

in homogeneous material)

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "-" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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Addendum-Page 2



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